(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
9 August 2012 (09.08.2012)

WIPO | PCT

(10) International Publication Number
WO 2012/106033 A3

(51) International Patent Classification:
H01L 21/3065 (2006.01)

(21) International Application Number:
PCT/US2011/064724

(22) International Filing Date:
13 December 2011 (13.12.2011)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
61/422,942 14 December 2010 (14.12.2010) US
13/197,487 3 August 2011 (03.08.2011) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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(54) Title: UNIFORM DRY ETCH IN TWO STAGES

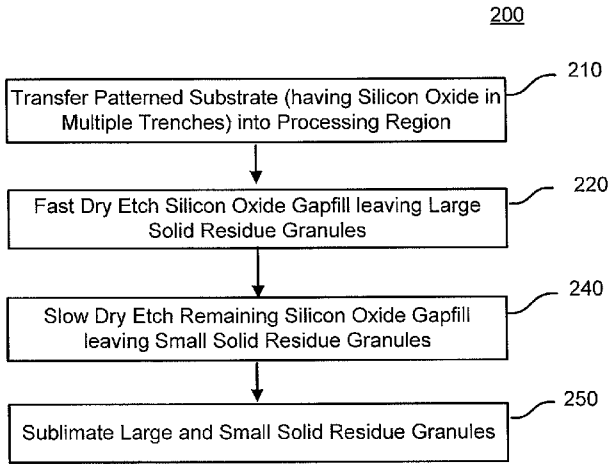


FIG. 2

(57) Abstract: A method of etching silicon oxide from a multiple trenches is described which allows more homogeneous etch rates among trenches. The surfaces of the etched silicon oxide within the trench following the etch may also be smoother. The method includes two dry etch stages followed by a sublimation step. The first dry etch stage removes silicon oxide quickly and produces large solid residue granules. The second dry etch stage remove silicon oxide slowly and produces small solid residue granules in amongst the large solid residue granules. Both the small and large solid residue are removed in the ensuing sublimation step. There is no sublimation step between the two dry etch stages.

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Declarations under Rule 4.17:

— *as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))*

Published:

— *with international search report (Art. 21(3))*

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*

(88) Date of publication of the international search report:
29 November 2012